[5] H. Raether, "Surface plasma oscillations and their applications," *Physics of Thin Films*, vol. 9, pp. 145–261, 1977.
[6] E. N. Economou, "Surface plasmons in thin films," *Phys. Rev.*, vol. 182, p. 539, 1969.
[7] Y. Y. Teng and E. A. Stern, "Plasma radiation from metal grating surfaces," *Phys. Rev. Lett.*, vol. 19, p. 511, 1967.
[8] A. Karp, "Backward-wave oscillator experiments at 100 to 200 kilomegacycles," *Proc. I.R.E.*, pp. 496–503, Apr. 1957.

Addendum to "Design of Microwave GaAs MESFET's for Broad-Band Low-Noise Amplifiers"

HATSUAKI FUKUI

It has been called to the author's attention that (3) in the above paper[1] appears to be inadequate [1], especially for scaling [2]. Considering this situation the expression should read

$$R_n = \frac{k_2}{g_m} \tag{3}$$

where $k_2 = 0.8$.

This modification leads to rewriting (12) as follows:

$$R_n = \frac{40}{Z}\left[\frac{aL}{N}\right]^{1/3} \Omega. \tag{12}$$

Consequently, the numerical values for R_n in Fig. 8 should be, in descending order, 46, 39, 33, 29, 25, 21, 18, and 15. Figs. 9 and 10 are also slightly affected by the revised expression. However, the principal statement and conclusions remain unchanged.

The author wishes to thank Dr. R. A. Pucel for his encouragement concerning this amendment.

References

[1] S. Weinreb, "Low-noise cooled GASFET amplifiers," *IEEE Trans. Microwave Theory Tech.*, vol. MTT-28, pp. 1041–1054, Oct. 1980.
[2] A. F. Podell, "A functional GaAs FET noise model," *IEEE Trans. Electron Devices*, vol. ED-28, pp. 511–517, May 1981.

Manuscript received June 3, 1981.
The author is with Bell Laboratories, Murray Hill, NJ 07974.
[1]Hatsuaki Fukui, *IEEE Trans. Microwave Theory Tech.*, vol. MTT-27, pp. 643–650, July 1979.

Correction to "Cylindrical Dielectric Resonators and their Applications in TEM Line Microwave Circuits"

MARIAN W. POSPIESZALSKI

In the above paper[1] the following correction should be made. Equation (3) should read as

$$F_0^2 = (u^2 + w^2)\frac{\epsilon_r}{\epsilon_r - 1}. \tag{3}$$

This is merely a typographical error and does not affect the other equations or results of the analysis.

Manuscript received June 3, 1981.
The author is with the Institute of Electronics Fundamentals, Warsaw Technical University, 00-665 Warsaw, Poland.
[1]M. W. Pospieszalski, *IEEE Trans. Microwave Theory Tech.*, vol. MTT-27, pp. 233–238, Mar. 1979.

Erratum to "Approximate Formulas for Line Capacitance and Characteristic Impedance of Microstrip Line"

S. Y. POH, W. C. CHEW, AND J. A. KONG

In the above paper [1], the approximate formula (42) for the characteristic impedance Z of a microstrip line, with substrate dielectric constant ϵ_r and thickness to width ratio h/W, should be

$$Z \simeq \frac{377}{\sqrt{\epsilon_r}}\frac{h}{W}\left\{1 - \frac{2}{\pi\epsilon_r}\left(\frac{h}{W}\right)\left[(1+\epsilon_r)\ln\left(\frac{2h}{W}\right) - 2.230 - 4.554\epsilon_r - (4.464 + 3.89\epsilon_r)\frac{h}{W}\right]\right\}^{-1/2}, \quad \text{for } h/W \text{ small.}$$

The approximate formula (44) for the line capacitance should be

$$\tilde{C} \approx \frac{\pi(1+\epsilon_r)h}{\epsilon_r W}\left\{\ln\left(\frac{8h}{W}\right) + \frac{1}{16(1+\epsilon_r)}\frac{W^2}{h^2} + \frac{\epsilon_r - 1}{\epsilon_r}\left[0.041(W/h)^2 - 0.454\right]\right\}^{-1}, \quad \text{for } h/W \text{ large.}$$

Manuscript received March 30, 1981.
The authors are with the Massachusetts Institute of Technology, Department of Electrical Engineering and Computer Science, Cambridge, MA 02139.
[1]S. Y. Poh *et al.*, *IEEE Trans. Microwave Theory Tech.*, vol. MTT-29, pp. 135–142, Feb. 1981.

0018-9480/81/1000-1119$00.75 ©1981 IEEE